Complementary Silicon High-Power Transistors

... PowerBase complementary transistors designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc—to—dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055 and MJ2955.

• Current-Gain — Bandwidth-Product @ IC = 1.0 Adc

 $f_T = 0.8 \text{ MHz (Min)} - \text{NPN}$

= 2.2 MHz (Min) - PNP

• Safe Operating Area — Rated to 60 V and 120 V, Respectively

*MAXIMUM RATINGS

Rating	Symbol	2N3055A MJ2955A	MJ15015 MJ15016	Unit
Collector–Emitter Voltage	VCEO	60 120		Vdc
Collector–Base Voltage	VCBO	100	200	Vdc
Collector–Emitter Voltage Base Reversed Biased	VCEV	100	200	Vdc
Emitter-Base Voltage	VEBO	7.0		Vdc
Collector Current — Continuous	IC	15		Adc
Base Current	ΙΒ	7.0		Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	115 0.65	180 1.03	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	0.98	°C/W

^{*} Indicates JEDEC Registered Data. (2N3055A)

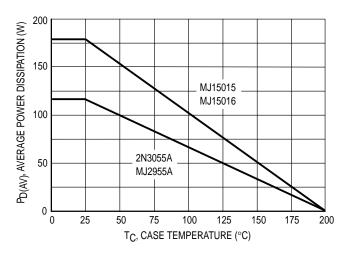


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

2N3055A MJ15015* MJ2955A PNP MJ15016*

*Motorola Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60, 120 VOLTS
115, 180 WATTS



CASE 1-07 TO-204AA (TO-3)



ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS (1)					
*Collector–Emitter Sustaining Voltage (I _C = 200 mAdc, I _B = 0)	2N3055A, MJ2955A MJ15015, MJ15016	VCEO(sus)	60 120	_ _	Vdc
Collector Cutoff Current (VCE = 30 Vdc, VBE(off) = 0 Vdc) (VCE = 60 Vdc, VBE(off) = 0 Vdc)	ICEO	_	0.7 0.1	mAdc	
*Collector Cutoff Current (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc)	2N3055A, MJ2955A MJ15015, MJ15016	ICEV	_	5.0 1.0	mAdc
Collector Cutoff Current (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc, T _C = 150°C)	ICEV	_ _	30 6.0	mAdc	
Emitter Cutoff Current (VEB = 7.0 Vdc, I _C = 0)	•			5.0 0.2	mAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base (t = 0.5 s non–repetitive) (VCE = 60 Vdc)	I _{S/b}	1.95 3.0		Adc	
ON CHARACTERISTICS (1)					
DC Current Gain (I _C = 4.0 Adc, V _{CE} = 2.0 Vdc) (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 10 Adc, V _{CE} = 4.0 Vdc)		hFE	10 20 5.0	70 70 —	_
Collector–Emitter Saturation Voltage (I _C = 4.0 Adc, I _B = 400 mAdc) (I _C = 10 Adc, I _B = 3.3 Adc) (I _C = 15 Adc, I _B = 7.0 Adc)		VCE(sat)	=	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 MHz)	fΤ	0.8 2.2	6.0 18	MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	60	600	pF
SWITCHING CHARACTERISTICS (2N3055A on	ly)			•	•
RESISTIVE LOAD					
Delay Time		t _d	_	0.5	μs
Rise Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 4.0 \text{ Adc},$	t _r	_	4.0	μs
Storage Time	$I_{B1} = I_{B2} = 0.4 \text{ Adc},$ $I_{D} = 25 \mu \text{s Duty Cycle} \le 2\%$	t _S	_	3.0	μs
Fall Time		t _f	_	6.0	μѕ

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%. * Indicates JEDEC Registered Data. (2N3055A)

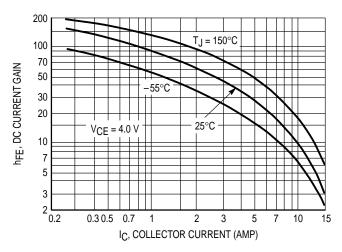
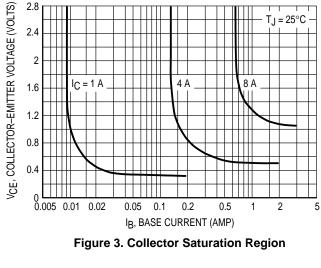


Figure 2. DC Current Gain



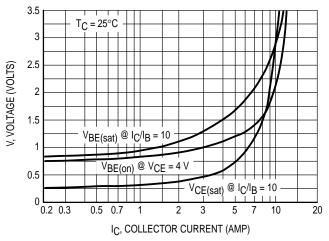


Figure 4. "On" Voltages

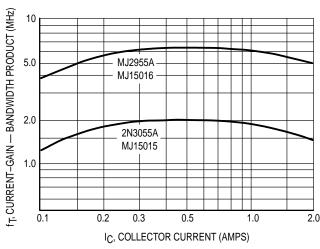


Figure 5. Current-Gain — Bandwidth Product

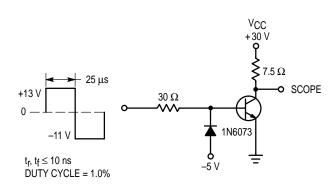


Figure 6. Switching Times Test Circuit (Circuit shown is for NPN)

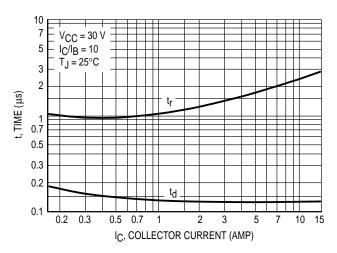


Figure 7. Turn-On Time

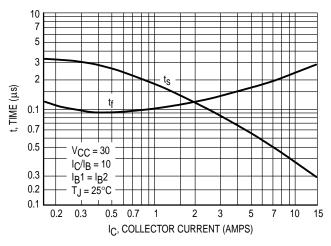


Figure 8. Turn-Off Times

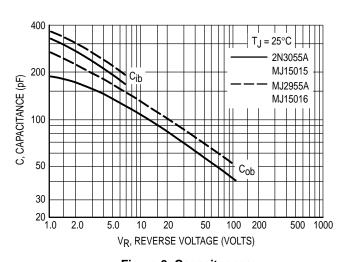


Figure 9. Capacitances

COLLECTOR CUT-OFF REGION

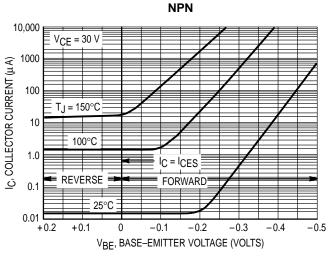


Figure 10. 2N3055A, MJ15015

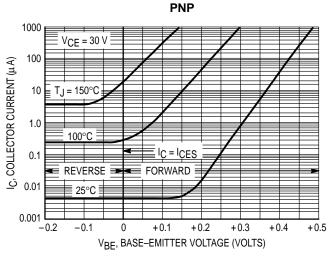


Figure 11. MJ2955A, MJ15016

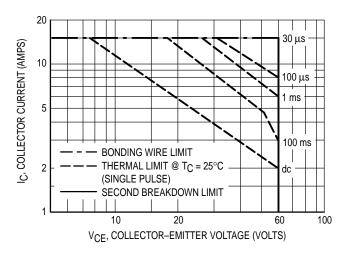


Figure 12. Forward Bias Safe Operating Area 2N3055A, MJ2955A

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipa-

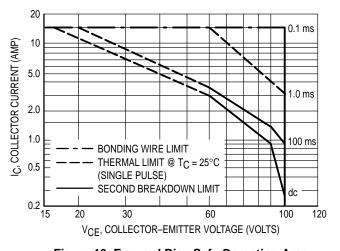
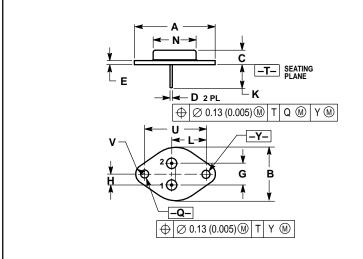


Figure 13. Forward Bias Safe Operating Area MJ15015, MJ15016

tion than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

		INCHES		MILLIN	IETERS	
DIN	١	MIN	MAX	MIN	MAX	
Α		1.550 REF		39.37 REF		
В			1.050		26.67	
С		0.250	0.335	6.35	8.51	
D		0.038	0.043	0.97	1.09	
E		0.055	0.070	1.40	1.77	
G		0.430 BSC		10.92 BSC		
Н		0.215 BSC		5.46 BSC		
K		0.440	0.480	11.18	12.19	
L		0.665 BSC		16.89 BSC		
N			0.830		21.08	
Q		0.151	0.165	3.84	4.19	
U		1.187 BSC		30.15 BSC		
٧	1	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

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